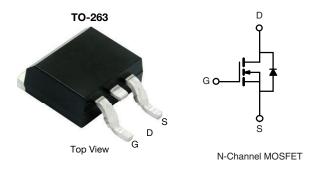


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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	60	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0020	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0025	
I _D (A)	120	
Configuration	Single	



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50020EL-GE3

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current ^a	T _C = 25 °C	1	120	
Continuous Drain Current "	T _C = 125 °C	I _D	120	
Continuous Source Current (Diode Conduction) a		I _S	120	Α
Pulsed Drain Current ^b		I _{DM}	300	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	75	
Single Pulse Avalanche Energy	L = U.1 IIII	E _{AS}	281	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D_	375	W
iviaximum rower bissipation ~	T _C = 125 °C	P_{D}	125	VV
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient PCI	B Mount ^c R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.4	G/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	1.5	mA
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	120	-	-	Α
		V _{GS} = 10 V	I _D = 30 A	-	0.0016	0.0020	
Dunin Course On State Presistance 2	В	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0031	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0037	Ω
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0020	0.0025	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	164	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	12 060	15 100	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	5750	7200	pF
Reverse Transfer Capacitance	C _{rss}]		-	860	1100	
Total Gate Charge ^c	Qg			-	128	200	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 80 \text{ A}$	-	33	-	nC
Gate-Drain Charge ^c	Q _{gd}]		-	11	-	
Gate Resistance	Rg		f = 1 MHz	0.8	1.68	2.6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	20	25	
Rise Time ^c	t _r	$V_{DD} =$	30 V, $R_L = 0.375 Ω$	-	15	40	1
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 80 A$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	65	100	ns
Fall Time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Chara	acteristics ^b	•					
Pulsed Current ^a	I _{SM}			-	-	300	Α
	1	I _F = 80 A, V _{GS} = 0 V				i	1

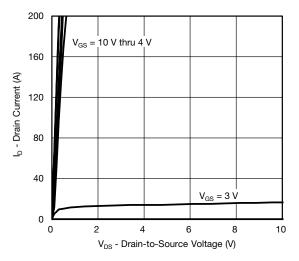
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

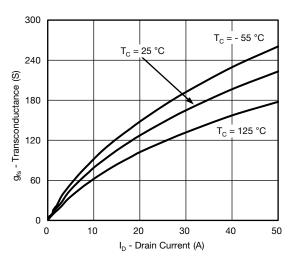
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



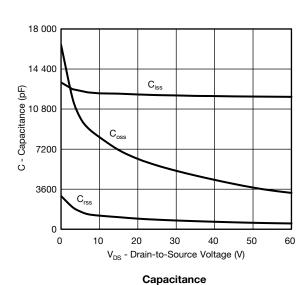
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

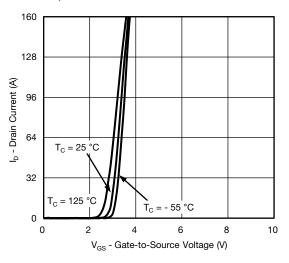


Output Characteristics

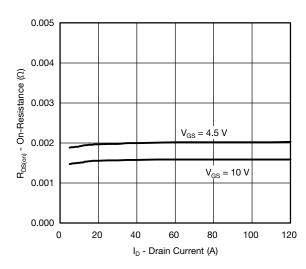


Transconductance

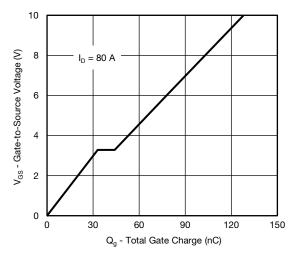




Transfer Characteristics

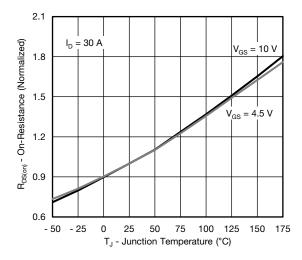


On-Resistance vs. Drain Current

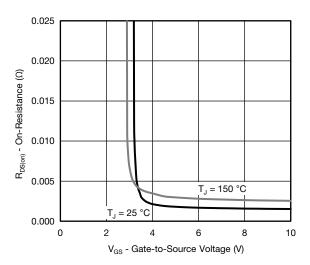




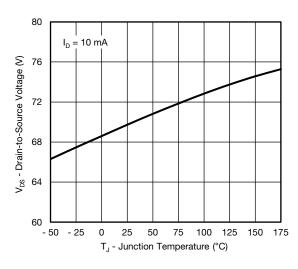
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



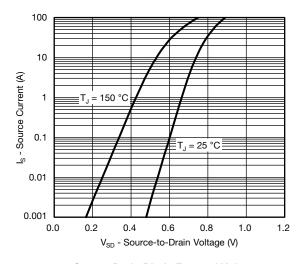
On-Resistance vs. Junction Temperature



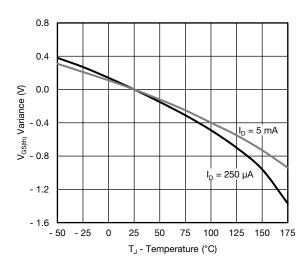
On-Resistance vs. Gate-to-Source Voltage



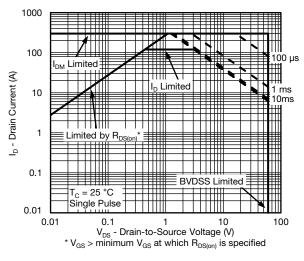
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



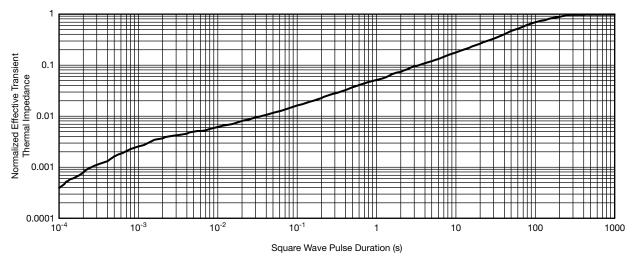
Threshold Voltage



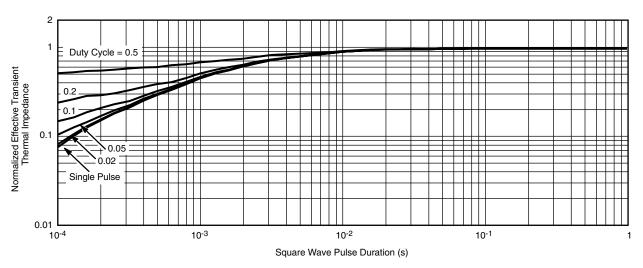
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

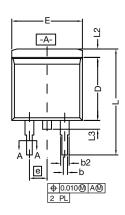
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

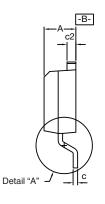
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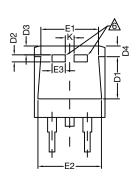
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TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

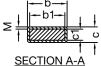








DETAIL A (ROTATED 90°)



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Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

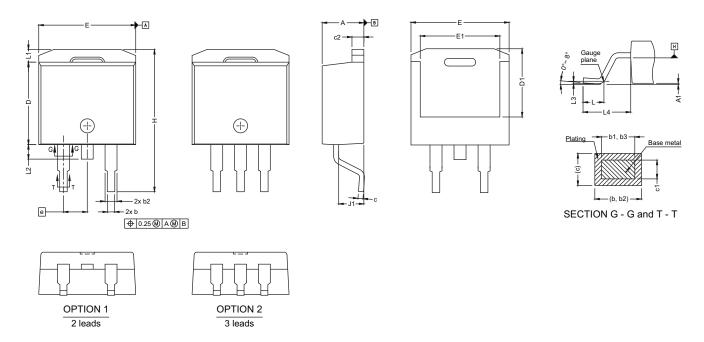
		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
	Α	0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
Ci	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25 typ.		
L4	4.78	5.28	
J1	2.56 2.96		

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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